Everspin Announces Production Release of 1 and 2 Gigabyte nvNITRO NVMe SSDs

Accelerators to be Showcased at Flash Memory Summit Aug 8-10 in Santa Clara California

Chandler, AZ, August 7, 2017 — Everspin Technologies, Inc. (NASDAQ: MRAM), the leading provider of MRAM solutions, today announced the production release of its nvNITRO™ line of storage accelerators, designed to deliver extremely fast read and write times with ultra-low latency. Everspin is launching the initial nvNITRO accelerators with 1GB and 2GB capacities, based on 256Mb DDR3 ST-MRAM. The storage accelerators are orderable today, and will ship in Q417. The nvNITRO accelerators operate up to 1.5 million IOPS with 6µs end-to-end latency. Everspin is delivering a half-height, half-length (HHHL) PCIe card as well as U.2 form factors; both support NVMe and memory mapped IO (MMIO) access modes.

Enterprise storage system vendors can now leverage MRAM's memory speed in traditional enterprise storage form factors and protocols. Everspin's ST-MRAM ensures that the data is persistent and power fail safe without the need for supercapacitors or battery backup, saving critical space in storage racks. The high cycle endurance of ST-MRAM also enables unlimited uniform drive writes per day, eliminating the need for complex wear-leveling algorithms that are required in NAND Flash-based drives. With Everspin's ST-MRAM endurance, there is no degradation in read/write performance over time.

> "Everspin is proud to announce the production release of our nvNITRO NVMe storage accelerators" said Phill LoPresti, Everspin's President and CEO. "We've enjoyed building the ecosystem with our partners to make Spin Torque MRAM a reality for today's storage market."
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> "Xilinx is pleased to see the combination of production-ready Spin Torque MRAM and our UltraScale™ FPGAs in the Everspin nvNITRO series. Coupling an ST-MRAM compatible memory controller with extended byte mode capabilities to an NVMe interface inside the Xilinx FPGA significantly reduces latency and simplifies the protection of mission-critical data," said Manish Muthal, Xilinx Vice President of Data Center.
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> "We are delighted to have co-developed this groundbreaking ST-MRAM nvNITRO Accelerator and are equally excited about its potential to be disruptive in the storage market" said Mike Rubino, SMART Modular Technologies Vice President of World Wide Engineering.

This high-end performance, combined with consistent ultra-low latency, means that demanding applications such as high frequency financial trading systems can depend on faster, more predictable transaction recording. The read/write speed combined with low latency brings significant value to many storage applications such as database and file system acceleration, online transaction processing log caches, and metadata caching/buffering. The need for higher speed across storage networks and data centers can now be met with the industry's first all-MRAM storage devices, providing both block access storage, and byte addressable memory functions on the same platform. The PCIe Gen 3, NVMe interface makes it simple to add this capability to existing storage networks and servers without the need for special drivers or operating system changes.

Key features & highlights include:

- 1GB and 2GB storage capacities
- PCIe Gen3 x8, half-height, half-length or U.2 form factor
- NVMe 1.1+ for block level access

- Memory mapped IO (MMIO) for byte level access
- 6µS Ultra-low access latency (as low as 2µS with SPDK drivers)
- Consistent latency (short tail)
- Customer-defined features using own RTL with programmable FPGA
- Inherently power fail safe; no system enablement required
- PCIe peer-to-peer communication for minimum processor overhead and lower latency
- ES1GB-N03 and ES2GB-N03 HHHL form factor
- ES1GB-U201 and 2GB ES2GB-U201 U.2 form factor
- Pricing starting at $2,200

Product Demonstrations in Booth #319 at Flash Memory Summit August 8-10

Everspin will be demonstrating its new products at Flash Memory Summit (FMS) in Santa Clara, California, August 8-10, 2017 in Everspin's booth (#319). FMS, held at the Santa Clara Convention Center, is an educational conference about the latest developments in flash memory hardware and software.

About Everspin Technologies

Everspin Technologies is the leading provider of Magnetoresistive RAM (MRAM) solutions. Everspin's MRAM solutions enable the protection of mission critical data by combining the persistence of non-volatile memory with the speed and endurance of SRAM or DRAM. Everspin's MRAM solutions allow its customers in the industrial, automotive, and enterprise storage markets to design high performance and reliable systems. Everspin is the only provider of commercially available MRAM solutions and has shipped over 70 million MRAM units. For more information, visit www.everspin.com.

Cautionary Statement Regarding Forward-Looking Statements

The statements in this press release regarding the development and production of Everspin's MRAM solutions are forward-looking statements that are subject to risks and uncertainties. Risks that could cause these forward-looking statements not to come true include, but are not limited to: the risk that unexpected technical difficulties may develop in the final stages of development or production of these products; and that customers may not perceive the benefits of Everspin's MRAM solutions to be as Everspin perceives them to be.

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